REMARKS

Favorable reconsideration and allowance of the claims of the present application are respectfully requested.

Before addressing the issues raised in the present Office Action, applicants acknowledge, with thanks, the Examiner's indication that Claims 24-35 are allowable and the Claims 2, 3, 8 and 9 would be allowable, if rewritten in independent form including all of the limitations of the base claim and any intervening claim.

In light of this indication of allowable subject matter, applicants have incorporated the features of Claims 2 and 3 into Claim 1 and have cancelled Claims 2 and 3. No further amendments to the remaining claims were made.

Applicants respectfully submit that the above amendment to Claim 1 to include the features of Claims 2 and 3 makes independent Claim 1, as well as dependent Claims 4-9, allowable.

Claims 1 and 4-7 stand rejected Under 35 U.S.C. § 103 as allegedly unpatentable over the combined disclosures of Japanese Patent No. 2001068708 ("JP '708") and U.S. Patent No. 5,677,992 to Hayafuji, et al. ("Hayafuji, et al.").

Applicants respectfully submit that the above amendment to Claim 1, which includes the allowable features of Claims 2 and 3, makes the obviousness rejection moot since the combined prior art references do not teach or suggest applicants' claimed structure. Specifically, the combined disclosures of JP '708 and Hayafuji, et al. do not teach or suggest applicants' claimed hybrid substrate comprising a first semiconductor layer having a first crystallographic orientation and a second semiconductor layer having a second crystallographic orientation which is different from the first crystallographic

orientation, wherein said first and second semiconductor layers are separated from each other by a conductive interface ***comprising a hydrophilic surface or a hydrophobic surface of at least one of said semiconductor layers.***

JP '708 discloses a structure having different semiconductor layers of different crystal orientation one on top of another. JP '708 does not disclose that a conductive interface is present between the two semiconductor layers.

Hayafuji, et al. disclose structure having semiconductor layers of different crystal orientation wherein cladding layers, which may be conductive, are located therebetween. The applied secondary reference, however, does not teach or suggest applicants' claimed conductive interface that includes a hydrophilic surface or a hydrophobic surface of one of the semiconductor layers.

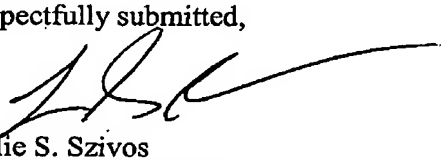
As such, and as recognized by the Examiner, the combined disclosures of JP '708 and Hayafuji, et al. do not render the claims of the present application unpatentable.

The § 103 rejection also fails because there is no motivation in the applied references which suggest modifying the disclosed structures to include the features now recited in Claim 1 of the instant application. Thus, there is no motivation provided in the applied references, or otherwise of record, to make the modification mentioned above. "The mere fact that the prior art may be modified in the manner suggested by the Examiner does not make the modification obvious unless the prior art suggested the desirability of the modification." In re Vaeck, 947 F.2d, 488, 493, 20 USPQ 2d. 1438, 1442 (Fed.Cir. 1991).

The rejection under 35 U.S.C. §103 has been obviated; therefore reconsideration and withdrawal thereof is respectfully requested.

Thus, in view of the foregoing amendments and remarks, it is firmly believed that the present case is in condition for allowance, which action is earnestly solicited.

Respectfully submitted,



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